

MSAEZ50N10A
MSAFZ50N10A

Features

- Ultrafast rectifier in parallel with the body diode (MSAE type only)
- Rugged polysilicon gate cell structure
- Increased Unclamped Inductive Switching (UIS) capability
- Hermetically sealed, surface mount power package
- Low package inductance
- Very low thermal resistance
- Reverse polarity available upon request

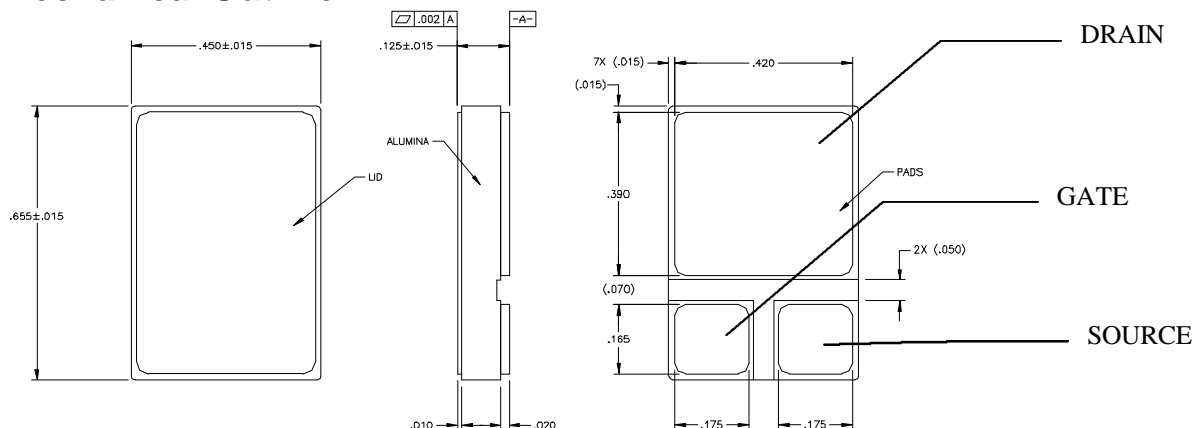
100 Volts
50 Amps
35 mΩ

N-CHANNEL
ENHANCEMENT MODE
POWER MOSFET

Maximum Ratings @ 25°C (unless otherwise specified)

| DESCRIPTION | SYMBOL | MAX. | UNIT |
|--|-------------------------|-------------|-------|
| Drain-to-Source Breakdown Voltage (Gate Shorted to Source) @ $T_J \geq 25^\circ\text{C}$ | BV_{DSS} | 100 | Volts |
| Drain-to-Gate Breakdown Voltage @ $T_J \geq 25^\circ\text{C}$, $R_{GS} = 1\text{ M}\Omega$ | BV_{DGR} | 100 | Volts |
| Continuous Gate-to-Source Voltage | V_{GS} | +/-20 | Volts |
| Transient Gate-to-Source Voltage | V_{GSM} | +/-30 | Volts |
| Continuous Drain Current 100°C | I_{D25} I_{D100} | 50 40 | Amps |
| Peak Drain Current, pulse width limited by T_{Jmax} | I_{DM} | 200 | Amps |
| Repetitive Avalanche Current | I_{AR} | 50 | Amps |
| Repetitive Avalanche Energy | E_{AR} | 18.5 | mJ |
| Single Pulse Avalanche Energy | E_{AS} | 400 | mJ |
| Voltage Rate of Change of the Recovery Diode @ $I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$ | dv/dt | TBD | V/ns |
| Power Dissipation | P_D | 300 | Watts |
| Junction Temperature Range | T_J | -55 to +150 | °C |
| Storage Temperature Range | T_{stg} | -55 to +150 | °C |
| Continuous Source Current (Body Diode) | I_S | 50 | Amps |
| Pulse Source Current (Body Diode) | I_{SM} | 200 | Amps |
| Thermal Resistance, Junction to Case | θ_{JC} | 0.4 | °C/W |

Mechanical Outline



MSAEZ50N10A MSAFZ50N10A

Electrical Parameters @ 25°C (unless otherwise specified)

| DESCRIPTION | SYMBOL | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|------------------------------|---|------|---------------------|------------------------|---------------|
| Drain-to-Source Breakdown Voltage (Gate Shorted to Source) | BV_{DSS} | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 100 | | | V |
| Temperature Coefficient of the Drain-to-Source Breakdown Voltage | $\Delta BV_{DSS}/\Delta T_J$ | | | TBD | | V/°C |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 1\ \text{mA}$ | 2.0 | 3.0 | 4.0 | V |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{GS} = \pm 20\text{V}_{DC}, V_{DS} = 0\ \text{T}_J = 25^\circ\text{C}$ $\text{T}_J = 125^\circ\text{C}$ | | | ± 100 ± 200 | nA |
| Drain-to-Source Leakage Current (Zero Gate Voltage Drain Current) | I_{DSS} | $V_{DS} = 0.8 \cdot BV_{DSS}\ \text{T}_J = 25^\circ\text{C}$ $V_{GS} = 0\ \text{T}_J = 125^\circ\text{C}$ | | | 25 250 | μA |
| Static Drain-to-Source On-State Resistance (1) | $R_{DS(on)}$ | $V_{GS} = 10\text{V}, I_D = 32\ \text{T}_J = 25^\circ\text{C}$ $I_D = 50\ \text{T}_J = 25^\circ\text{C}$ $I_D = 32\ \text{T}_J = 125^\circ\text{C}$ | | 0.03 TBD 0.05 | 0.035 | Ω |
| Forward Transconductance (1) | g_{fs} | $V_{DS} \geq 15\ \text{V}; I_D = 32\ \text{A}$ | 15 | 28 | | S |
| Input Capacitance | C_{iss} | $V_{GS} = 0\ \text{V}, V_{DS} = 25\ \text{V}, f = 1\ \text{MHz}$ | | 2400 | 3200 | μF |
| Output Capacitance | C_{oss} | | | 730 | 1100 | |
| Reverse Transfer Capacitance | C_{rss} | | | 430 | 650 | |
| Turn-on Delay Time | $T_{d(on)}$ | $V_{GS} = 10\ \text{V}, V_{DS} = 30\ \text{V},$ $I_D = 3\ \text{A}, R_G = 50\ \Omega$ | | 33 | 50 | ns |
| Rise Time | t_r | | | 140 | 210 | |
| Turn-off Delay Time | $t_{d(off)}$ | | | 500 | 670 | |
| Fall Time | t_f | | | 230 | 310 | |
| Total Gate Charge | $Q_{g(on)}$ | $V_{GS} = 10\ \text{V}, V_{DS} = 80\text{V}, I_D = 30\text{A}$ | | 225 | | nC |
| Gate-to-Source Charge | Q_{gs} | | | 20 | | |
| Gate-to-Drain (Miller) Charge | Q_{gd} | | | 100 | | |
| Body Diode Forward Voltage (1) | V_{SD} | $I_F = I_S, V_{GS} = 0\ \text{V}$ | | | 1.2 1.8 | V |
| Reverse Recovery Time (Body Diode) | t_{rr} | $I_F = 10\ \text{A},$ $-di/dt = 100\ \text{A}/\mu\text{s},$ | MSAE | | 50 | ns |
| | | | MSAF | | 170 | |
| Reverse Recovery Charge | Q_{rr} | $I_F = 10\ \text{A},$ $di/dt = 100\ \text{A}/\mu\text{s},$ | | | tbd 0.9 | μC |

Notes

- (1) Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\delta \leq 2\%$
- (2) Microsemi Corp. does not manufacture the mosfet die; contact company for details.